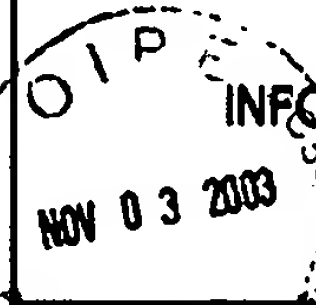


QUERY CONTROL FORM		RTIS USE ONLY	
Application No. <u>09/896 W/C</u>	Prepared by <u>C. Majors</u>	Tracking Number <u>05877408</u>	
Examiner-GAU <u>Pert - 8829</u>	Date <u>1/8/04</u>	Week Date <u>12/15/03</u>	
	No. of queries <u>1</u>	<u>IFW</u>	

JACKET			
a. Serial No.	f. Foreign Priority	k. Print Claim(s)	p. <u>PTO-1449</u>
b. Applicant(s)	g. Disclaimer	l. Print Fig.	q. PTOL-85b
c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract
d. PCT	i. Title	n. PTO-270/328	s. Sheets/Figs
e. Domestic Priority	j. Claims Allowed	o. PTO-892	t. Other

[illegible]

 INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	ATTY DOCKET NO. ITO.0527US (P11412)	SERIAL NO. 09/896,616
	APPLICANT(S): TYLER A. LOWREY	
	FILING DATE: June 30, 2001	GROUP ART UNIT: 2829

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.						
	B.						
	C.						
	D.						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	E.							
	F.							
	G.							
	H.							

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	I.	Hwang, Y.N., Hong, J.S., Lee, S.H., Ahn, S.J., Jeong, G.T., Koh, G.H., Kim, H.J., Jeong, W.C., Lee, S.Y., Park, J.H., Ryoo, K.C., Horii, H., Ha, Y.H., Yi, J.H., Cho, W.Y., Kim, Y.T., Lee, K.H., Joo, S.H., Park, S.O., Jeong, U.I., Jeong, H.S. and Kim, Kinam, "Completely CMOS-Compatible Phase-Change Nonvolatile RAM Using NMOS Cell Transistors," presented at 2003 19 th IEEE Non-Volatile Semiconductor Memory Workshop, Monterey, California, February 26-20, 2003
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	M.	
	N.	
	O.	

EXAMINER	DATE CONSIDERED
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.